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3. (Amended) A semiconductor device comprising:  
a Si crystal having a (111) surface; and  
an insulation film formed on said (111) surface of said Si crystal,  
wherein at least a part of said insulation film comprises a Si oxide film containing Kr,  
and a Kr concentration level decreases in said Si oxide film from a surface of said Si oxide  
film to an interface between said Si oxide film and said Si crystal.
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*See the attached Appendix for the changes made to effect the above claims.*

Please add the following new claims:

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40. (New) A semiconductor device comprising:  
a Si crystal having a (111) surface; and  
an insulation film formed on said (111) surface of said Si crystal,  
wherein at least a part of said insulation film comprises a Si oxide film containing Kr,  
wherein said Kr reduces current leakage and improves breakdown characteristics of said  
insulation film when formed on said (111) surface of said Si crystal.
41. (New) A semiconductor device as claimed in claim 40, wherein said Si oxide film has  
a surface state density of  $10^{11} \text{ eV}^{-2} \text{ cm}^{-2}$  or less.
42. (New) A semiconductor device as claimed in claim 40, wherein a Kr concentration  
level decreases in said Si oxide film from a surface of said Si oxide film to an interface  
between said Si oxide film and said Si crystal.
43. (New) A semiconductor device as claimed in claim 40, wherein said Si oxide film  
contains Kr with a surface density of  $5 \times 10^{11} \text{ cm}^{-2}$  or less at a surface thereof.
44. (New) A semiconductor device as claimed in claim 40, further comprising a gate  
electrode on said Si oxide film.

45. (New) A semiconductor device as claimed in claim 40, wherein said crystal surface is formed on a part of a device isolation groove formed on said Si crystal.

46. (New) A semiconductor device as claimed in claim 40, wherein said crystal surface forms a principal surface of said Si crystal.

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